

INFORMATION DISCLOSURE STATEMENT

CASE: 12-14-9-7-5

SERIAL NO.:

69-433,201

APPLICANT: Robert Alan Hamm et al

FILING DATE:

GROUP:

jc525 U.S. PTO
09/433204

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Examiner: Initial box if reference is considered, whether or not citation is in conformance with MPEP 609. Draw a line through citation if not in conformance and not considered. Include a copy of this form with next communication to applicant.

U.S. PATENT DOCUMENTS

HAMS
1-7-00
ACONT

☒ AA: Patent No. 4,214,966, filed on March 29, 1979 and issued on July 29, 1980 to Mahoney, G. E. Class: 204/192.

☒ AB: Patent No. 4,301,188, filed on October 1, 1979 and issued on November 17, 1981 to Niehaus, W. C. Class: 427/88.

☒ AC: Patent No. 5,620,909, filed on December 4, 1995 and issued on April 15, 1997 to Lin, J. et al. Class: 438/703.

☒ AD: Patent No. 5,656,515, filed on July 18, 1996 and issued on August 12, 1997 to Chandrasekhar, M. et al. Class: 438/319.

☒ AE: Patent No. 5,625,206, filed on June 3, 1996 and issued on April 29, 1997 to Chandrasekhar, S. et al. Class: 257/198.

☒ AF: Patent No. 5,903,037, filed on February 24, 1997 and issued on May 11, 1999 to Cho, A. Y. et al. Class: 257/410.

☒ AG: Patent No. 5,907,165, filed on May 1, 1998 and issued on May 25, 1999 to Hamm, R. A. et al. Class: 257/197.

OTHER DOCUMENTS

☒ AH: "Evaluation of Encapsulation and Passivation of InGaAs/InP DHBT Devices for Long-Term Reliability", by Kopf, R. F. et al., *Journal of Electronic Materials*, Vol. 27, No. 8, pp. 954-960 (1998).

☒ AI: "ECR Plasma Etch Fabrication of C-Doped Base InGaAs/InP DHBT Structures: A Comparison of CH₄/H₂/Ar vs BCl₃/N₂ Plasma Etch Chemistries", by Kopf, R. F. et al., *Journal of Electronic Materials*, Vol 27, pp. 69-72 (1998).

☒ AJ: "Gallium Arsenide Processing Techniques", by Williams, R. E., published by The Artech Microwave Library, pp. 126-129.

Att: References as noted above

Examiner:

T. DANG

Date:

6/30/01